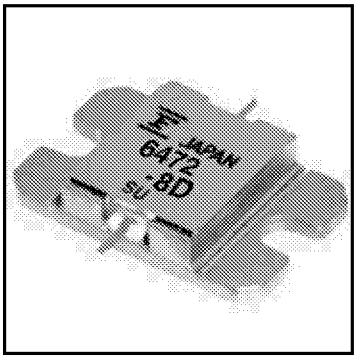
FLM6472-8D
Internally Matched Power GaAs FETs

FUJITSU

FEATURES

- High Output Power: P_{1dB} = 39dBm (Typ.)
- High Gain: G_{1dB} = 7.0dB (Typ.)
- High PAE: η_{add} = 29% (Typ.)
- Low IM_3 = -45dBc@Po = 28dBm
- Broad Band: 6.4 ~ 7.2GHz
- Impedance Matched Zin/Zout = 50Ω
- Hermetically Sealed Package



DESCRIPTION

The FLM6472-8D is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature Ta=25°C)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	T_C = 25°C	42.8	W
Storage Temperature	T_{stg}		-65 to +175	°C
Channel Temperature	T_{ch}		175	°C

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 16.0 and -4.4 mA respectively with gate resistance of 100Ω.

ELECTRICAL CHARACTERISTICS (Ambient Temperature Ta=25°C)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	V_{DS} = 5V, V_{GS} = 0V	-	3600	5400	mA
Transconductance	g_m	V_{DS} = 5V, I_{DS} =2200mA	-	2000	-	mS
Pinch-off Voltage	V_p	V_{DS} = 5V, I_{DS} =180mA	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	V_{GSO}	I_{GS} = -180μA	-5	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	V_{DS} =10V, I_{DS} = 0.6 I_{DSS} (Typ.), f = 6.4 ~ 7.2 GHz, Z_S=Z_L=50 ohm	38	39	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		6.0	7.0	-	dB
Drain Current	I_{dsr}		-	2200	2600	mA
Power-added Efficiency	η_{add}		-	29	-	%
Gain Flatness	ΔG		-	-	±0.6	dB
3rd Order Intermodulation Distortion	IM_3	f = 7.2 GHz, Δf = 10 MHz 2-Tone Test P_{out} = 28dBm S.C.L.	-42	-45	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	3.0	3.5	°C/W

CASE STYLE: IB

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

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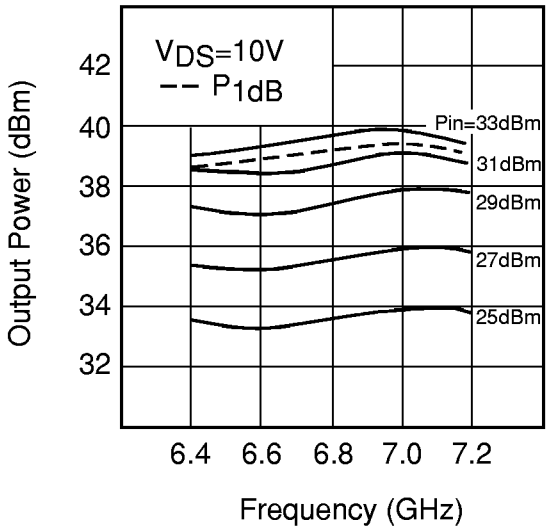
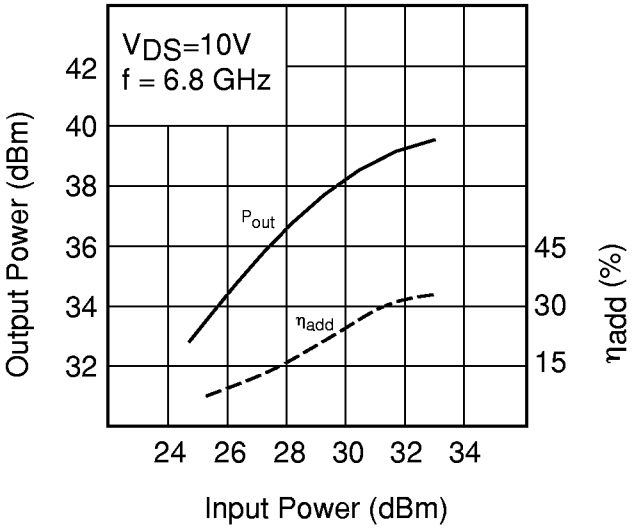
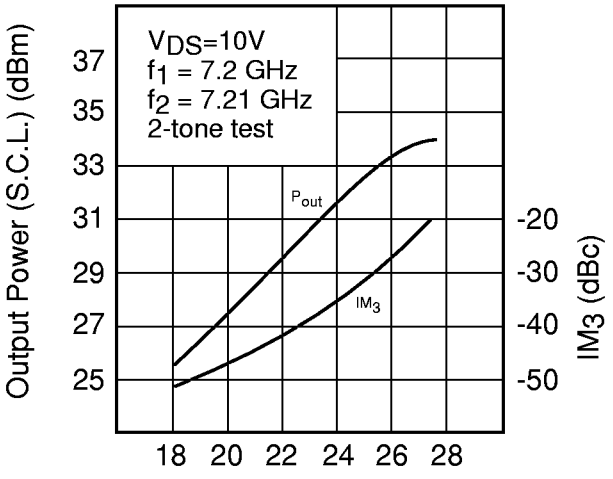
OUTPUT POWER vs. FREQUENCY

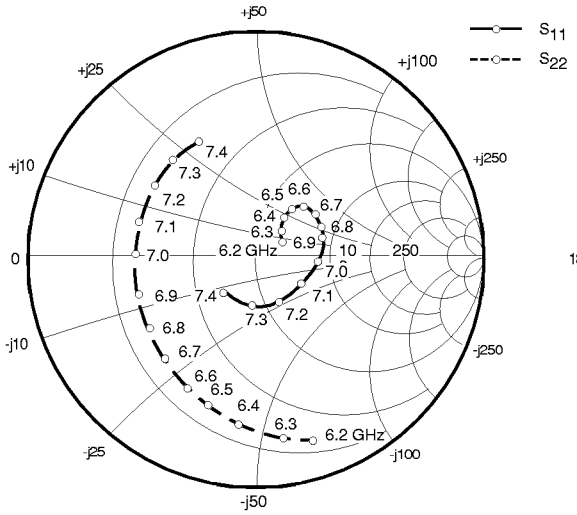


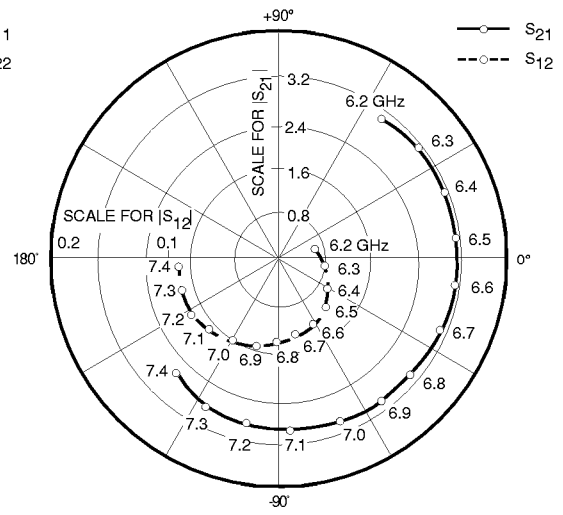
OUTPUT POWER vs. INPUT POWER



OUTPUT POWER & IM3 vs. INPUT POWER







S-PARAMETERS

V_{DS} = 10V, I_{DS} = 2200mA

FREQUENCY	S11		S21		S12		S22	
(MHZ)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6300	.15	47	3.11	34	.04	-8	.78	-79
6400	.20	55	3.11	18	.05	-28	.73	-94
6500	.25	52	3.17	4	.05	-45	.68	-108
6600	.29	47	3.16	-8	.06	-61	.65	-119
6700	.31	37	3.14	-23	.06	-78	.59	-133
6800	.31	26	3.04	-40	.07	-93	.56	-147
6900	.30	14	3.06	-55	.07	-104	.52	-163
7000	.27	-3	3.01	-69	.08	-120	.52	179
7100	.24	-26	2.97	-85	.08	-133	.51	165
7200	.20	-57	2.82	-103	.09	-147	.52	147
7300	.19	-96	2.77	-117	.09	-160	.53	131
7400	.23	-137	2.63	-132	.08	-175	.55	113

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Case Style "IB"
Metal-Ceramic Hermetic Package